

isc Silicon NPN Power Transistor

2SC2073

DESCRIPTION

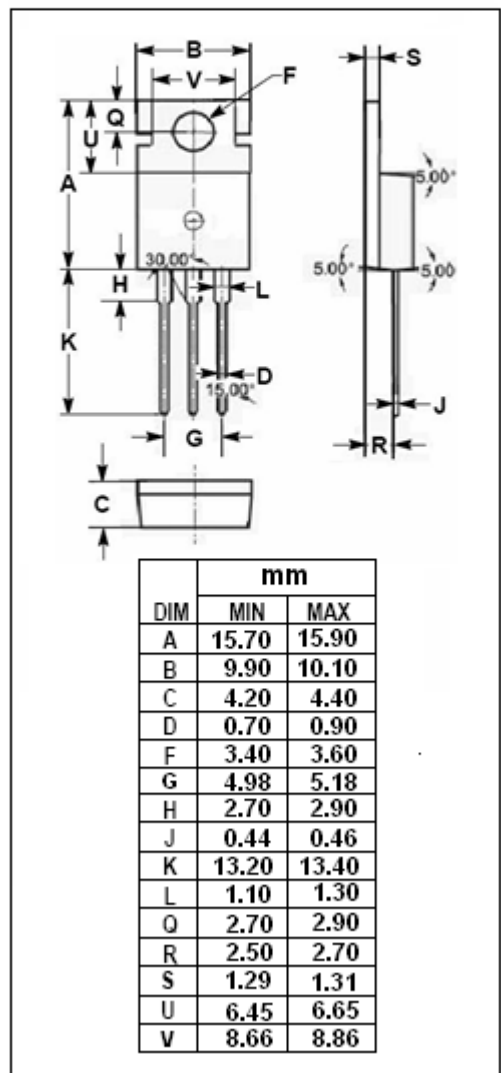
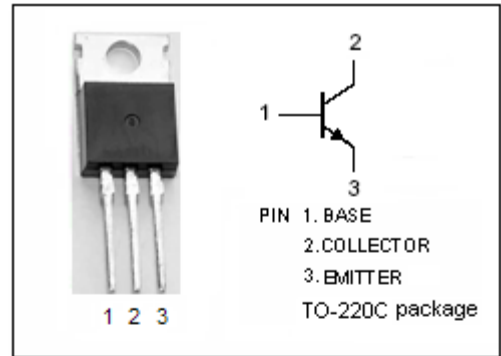
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 150V(\text{Min})$
- Wide Area of Safe Operation
- Complement to Type 2SA940

APPLICATIONS

- Power amplifier applications.
- Vertical output applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	1.5	A
$I_B$	Base Current-Continuous	0.5	A
$P_C$	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.5	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	25	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SC2073****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=500\text{mA}; I_B=50\text{mA}$			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=500\text{mA}; V_{CE}=10\text{V}$			0.85	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=120\text{V}; I_E=0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C=500\text{mA}; V_{CE}=10\text{V}$	40		140	
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		35		pF
$f_T$	Current-Gain—Bandwidth Product	$I_C=500\text{mA}; V_{CE}=10\text{V}$		4		MHz